

**MPSA92
MPSA93**

**SILICON
HIGH VOLTAGE
PNP TRANSISTORS**



TO-92 CASE

DESCRIPTION:

The CENTRAL SEMICONDUCTOR MPSA92 and MPSA93 are silicon PNP transistors designed for high voltage applications.

MARKING: FULL PART NUMBER

MAXIMUM RATINGS: ($T_A=25^\circ\text{C}$ unless otherwise noted)

	SYMBOL	MPSA92	MPSA93	UNITS
Collector-Base Voltage	V_{CBO}	300	200	V
Collector-Emitter Voltage	V_{CEO}	300	200	V
Emitter-Base Voltage	V_{EBO}	5.0		V
Continuous Collector Current	I_C	500		mA
Power Dissipation	P_D	625		mW
Power Dissipation ($T_C=25^\circ\text{C}$)	P_D	1.5		W
Operating and Storage Junction Temperature	T_J, T_{stg}	-65 to +150		$^\circ\text{C}$
Thermal Resistance	θ_{JA}	200		$^\circ\text{C/W}$
Thermal Resistance	θ_{JC}	83.3		$^\circ\text{C/W}$

ELECTRICAL CHARACTERISTICS: ($T_A=25^\circ\text{C}$)

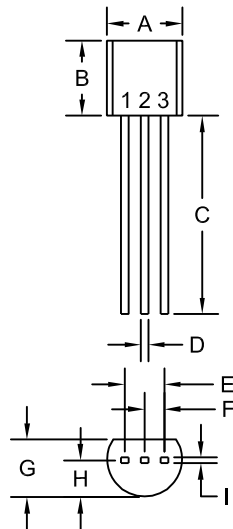
SYMBOL	TEST CONDITIONS	MPSA92		MPSA93		UNITS
		MIN	MAX	MIN	MAX	
I_{CBO}	$V_{CB}=200\text{V}$	-	250	-	-	nA
I_{CEO}	$V_{CE}=160\text{V}$	-	-	-	250	nA
I_{EBO}	$V_{EB}=3.0\text{V}$	-	100	-	100	nA
BV_{CBO}	$I_C=100\mu\text{A}$	300	-	200	-	V
BV_{CEO}	$I_C=1.0\text{mA}$	300	-	200	-	V
BV_{EBO}	$I_E=100\mu\text{A}$	5.0	-	5.0	-	V
$V_{CE(SAT)}$	$I_C=20\text{mA}, I_B=2.0\text{mA}$	-	0.5	-	0.4	V
$V_{BE(SAT)}$	$I_C=20\text{mA}, I_B=2.0\text{mA}$	-	0.9	-	0.9	V
h_{FE}	$V_{CE}=10\text{V}, I_C=1.0\text{mA}$	25	-	25	-	
h_{FE}	$V_{CE}=10\text{V}, I_C=10\text{mA}$	40	-	40	-	
h_{FE}	$V_{CE}=10\text{V}, I_C=30\text{mA}$	25	-	25	-	
f_T	$V_{CE}=20\text{V}, I_C=10\text{mA}, f=100\text{MHz}$	50	-	50	-	MHz
C_{ob}	$V_{CB}=20\text{V}, I_E=0, f=1.0\text{MHz}$	-	6.0	-	8.0	pF

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TO-92 CASE - MECHANICAL OUTLINE



R1

SYMBOL	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A (DIA)	0.175	0.205	4.45	5.21
B	0.170	0.210	4.32	5.33
C	0.500	-	12.70	-
D	0.016	0.022	0.41	0.56
E	0.100		2.54	
F	0.050		1.27	
G	0.125	0.165	3.18	4.19
H	0.080	0.105	2.03	2.67
I	0.015		0.38	

TO-92 (REV: R1)

LEAD CODE:

- 1) Emitter
- 2) Base
- 3) Collector

MARKING:

FULL PART NUMBER

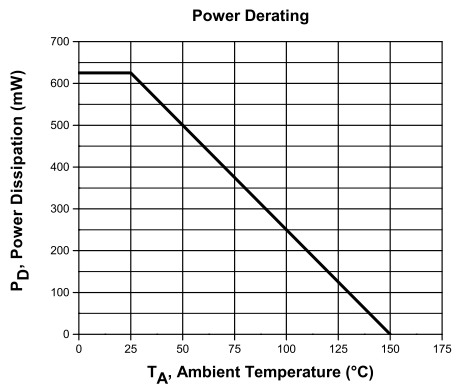
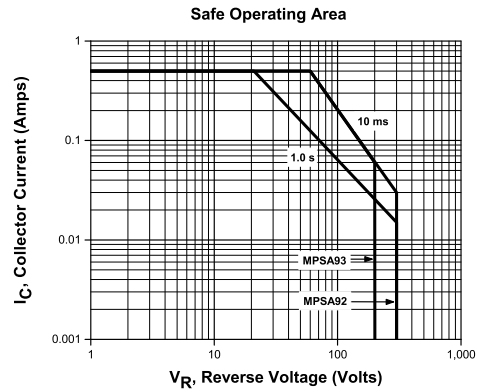
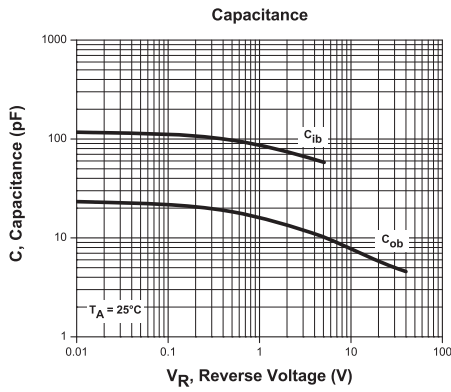
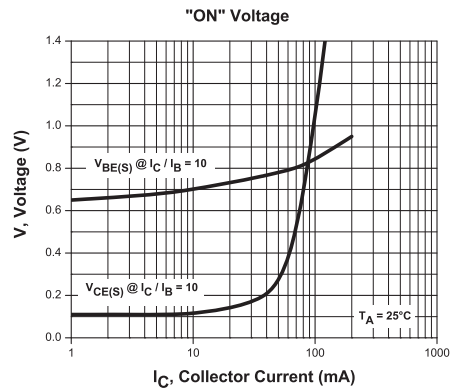
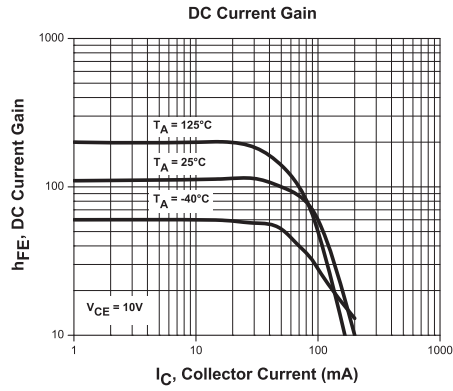
R2 (15-December 2014)

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TYPICAL ELECTRICAL CHARACTERISTICS



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SERVICES

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